

PRM012N04S8

PFC Device Corporation

40V Single N-Channel MOSFET

Major ratings and characteristics

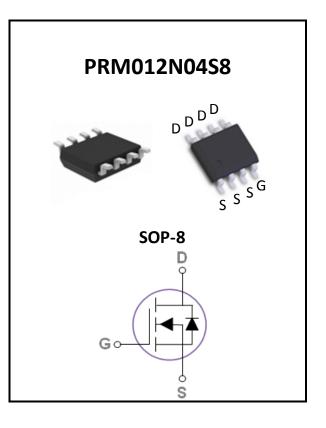
| Characteristics | Values | Units |
|--|-------------|-------|
| V _{DS} | 40 | V |
| I _D (T _A =25°C) | 10.7 | Α |
| Max. R _{DS(ON)} @V _{GS} =10V | 12 | mΩ |
| Max. $R_{DS(ON)}@V_{GS}=4.5V$ | 17 | mΩ |
| T _J Operating Junction Temperature | -55 to +150 | °C |

General Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.

Typical Applications

- Charger Adapter
- Power Tools
- LED Lighting



Features

- Max. $R_{DS(ON)}=12m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% E_{AS} Guaranteed
- Green Device Available

1. Characteristics

Maximum Ratings Characteristics

($T_A = 25$ °C unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|------------------|--|------------|-------|
| V_{DS} | Drain-Source Voltage | 40 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| | Drain Current – Continuous (T _A =25°C) | 10.7 | А |
| Ι _D | Drain Current – Continuous (T _A =100°C) | 6.7 | А |
| I _{DM} | Drain Current – Pulsed ¹ | 42.8 | А |
| E _{AS} | Single Pulse Avalanche Energy ² | 5 | mJ |
| I _{AS} | Single Pulse Avalanche Current ² | 10 | А |
| Р | Power Dissipation (T _A =25°C) | 2.5 | W |
| P _D | Power Dissipation – Derate above 25°C | 0.02 | W/°C |
| T _{STG} | Storage Temperature Range | -55 to 150 | °C |
| TJ | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Characteristics

| Symbol | Parameter | Тур. | Max. | Unit |
|------------------|--|------|------|------|
| R _{θJA} | Thermal Resistance Junction to Ambient | | 50 | °C/W |



Electrical Characteristics

($T_J = 25$ °C unless otherwise specified)

Off Characteristics

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|------------------|--------------------------------|--|------|------|------|------|
| BV_{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 40 | | | V |
| | Drain Source Leekage Current | V _{DS} =40V, V _{GS} =0V, T _J =25°C | | | 1 | uA |
| IDSS | Drain-Source Leakage Current | V _{DS} =40V, V _{GS} =0V, T _J =125°C | | | 250 | uA |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | | | ±100 | nA |

On Characteristics

| R _{DS(ON)} Static Drain-Source On-Resistance | V _{GS} =10V, I _D =5A | | | 12 | mΩ | |
|---|--|--|-----|----|-----|----|
| R _{DS(ON)} | | V _{GS} =4.5V, I _D =3A | | | 17 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 1.0 | | 3.0 | V |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =5A | | 19 | | S |

Dynamic and switching Characteristics

| Q _g | Total Gate Charge | V _{DS} =20V, V _{GS} =10V, I _D =10.7A | 24 | |
|---------------------|------------------------------|---|----------|---------|
| Q _{gs} | Gate-Source Charge | | 4.5 | nC |
| Q _{gd} | Gate-Drain Charge | | 4 | |
| T _{d(on)} | Turn-On Delay Time | | 11 | |
| Tr | Turn-On Rise Time | V_{DD} =20V, V_{GS} =10V, R_{G} =6 Ω I_{D} =10.7A | 56 | ns |
| T _{d(off)} | Turn-Off Delay Time | | 29 | 115 |
| T _f | Turn-Off Fall Time | | 55 | |
| C _{iss} | Input Capacitance | | 1390 | |
| C _{oss} | Output Capacitance | V _{DS} =25V, V _{GS} =0V, f=1MHz | 100 | pF |
| C _{rss} | Reverse Transfer Capacitance | | 75 | |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | 2 | Ω |

Drain-Source Diode Characteristics

| V _{SD} ³ | Source to Drain Diode Voltage | V _{GS} =0V, I _S =10.7A | | 1.5 | V |
|------------------------------|-------------------------------|--|-------|-----|----|
| t _{rr} | Reverse Recovery Time | I _s =10A, di/dt=100A/us | 7 | | ns |
| Q _{rr} | Reverse Recovery Charge | $I_{\rm S}$ = 10A, u/ul= 100A/us | 1 | | nC |

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.

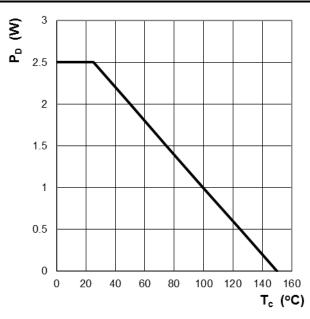
2. L=0.1mH, R_G =25 Ω , Starting T_J=25°C

3. The data tested by pulsed , pulse width $\leq\!\!300us$, duty cycle $\leq\!\!2\%$





Ratings and Characteristics Curves





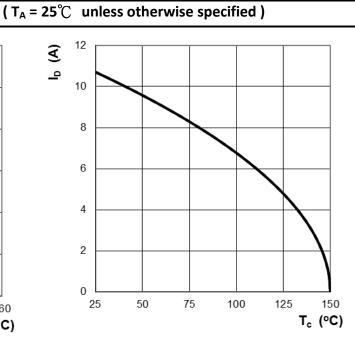
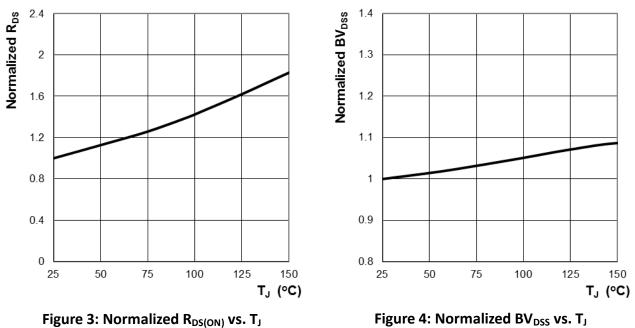
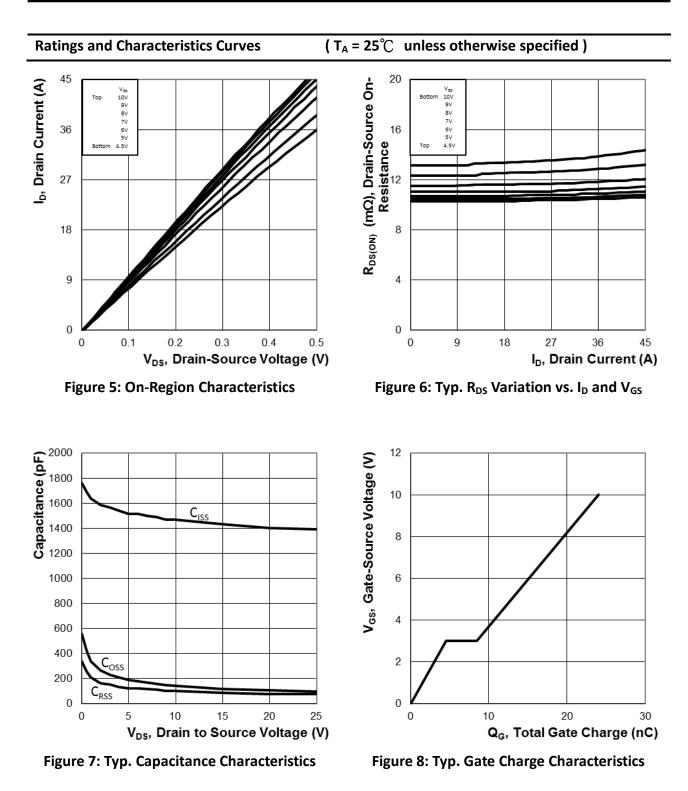


Figure 2: Continuous Drain Current vs. T_c

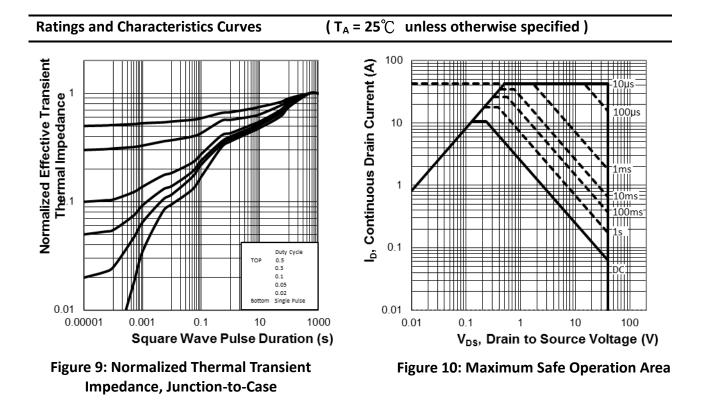








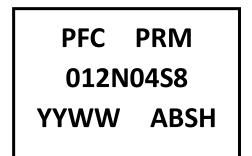






3. Marking information

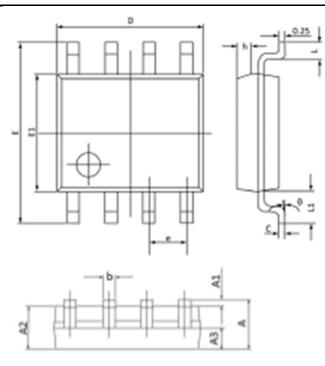
Top Marking Rule



PRM012N04S8 = Product Type Marking Code YYWW = Date Code YY = Last two digits of year WW = Week code ABS = Assembly code H = Halogen Free (N/A = common molding compound)

4. Package information

Package Outline Dimensions millimeters



| Dim. | Min. | Max. | | |
|----------------------|----------|------|--|--|
| Α | 1.35 | 1.75 | | |
| Al | 0.10 | 0.25 | | |
| A2 | 1.30 | | | |
| A3 | 0.60 | 0.70 | | |
| b | 0.35 | 0.49 | | |
| С | 0.18 | 0.26 | | |
| D | 4.70 | 5.10 | | |
| E | 5.80 | 6.20 | | |
| El | 3.70 | 4.10 | | |
| e | 1.27 | BSC | | |
| h | 0.25 | 0.50 | | |
| L | 0.40 | 0.90 | | |
| Ll | 1.05 BSC | | | |
| θ | 0° | 8° | | |
| All Dimensions in mm | | | | |



5. Ordering information

| Part Number | Package | Delivery mode |
|-------------|---------|------------------------------|
| PRM012N04S8 | SOP-8 | 3000 pcs / 13" diameter reel |

Mechanical

- Molder Plastic: UL Flammability Classification Rating 94V-0
- Device Weight: 0.003 ounces (0.085grams) SOP-8

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